

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous diode forward current	I_S	$T_C=25\text{ °C}$	2	A
Diode pulse current ²⁾	$I_{S,pulse}$		6	
Reverse diode dv/dt ⁴⁾	dv/dt		4	V/ns

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		-	-	3	K/W
Thermal resistance, junction - ambient	R_{thJA}	SMD version, device on PCB, minimal footprint	-	-	62	
		SMD version, device on PCB, 6 cm ² cooling area ⁵⁾	-	35	-	
Soldering temperature, reflow soldering	T_{solder}	reflow MSL1	-	-	260	°C

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}$, $I_D=250\text{ }\mu\text{A}$	800	-	-	V
Avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS}=0\text{ V}$, $I_D=2\text{ A}$	-	870	-	
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=0.12\text{ mA}$	2.1	3	3.9	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=800\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$	-	-	5	μA
		$V_{DS}=800\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=150\text{ °C}$	-	25	-	
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}$, $I_D=1.2\text{ A}$, $T_j=25\text{ °C}$	-	2.4	2.7	Ω
		$V_{GS}=10\text{ V}$, $I_D=1.2\text{ A}$, $T_j=150\text{ °C}$	-	6.5	-	
Gate resistance	R_G	$f=1\text{ MHz}$, open drain	-	1.2	-	Ω

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=100\text{ V},$ $f=1\text{ MHz}$	-	290	-	pF
Output capacitance	C_{oss}		-	13	-	
Effective output capacitance, energy related ⁶⁾	$C_{o(er)}$	$V_{GS}=0\text{ V}, V_{DS}=0\text{ V}$ to 480 V	-	11	-	
Effective output capacitance, time related ⁷⁾	$C_{o(tr)}$		-	26	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=400\text{ V},$ $V_{GS}=0/10\text{ V}, I_D=2\text{ A},$ $R_G=47\text{ }\Omega, T_j=25\text{ }^\circ\text{C}$	-	25	-	ns
Rise time	t_r		-	15	-	
Turn-off delay time	$t_{d(off)}$		-	72	-	
Fall time	t_f		-	18	-	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD}=640\text{ V}, I_D=2\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	1.5	-	nC
Gate to drain charge	Q_{gd}		-	6	-	
Gate charge total	Q_g		-	12	16	
Gate plateau voltage	$V_{plateau}$		-	5.5	-	V

Reverse Diode

Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=I_S=2\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	-	1	1.2	V
Reverse recovery time	t_{rr}	$V_R=400\text{ V}, I_F=I_S=2\text{ A},$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	520	-	ns
Reverse recovery charge	Q_{rr}		-	2	-	μC
Peak reverse recovery current	I_{rrm}		-	6	-	A

¹⁾ J-STD20 and JESD22

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Repetitive avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR} \cdot f$.

⁴⁾ $I_{SD}=I_D, di/dt=400\text{ A}/\mu\text{s}, V_{DClink}=400\text{ V}, V_{peak}<V_{(BR)DSS}, T_j<T_{j,max}$, identical low side and high side switch

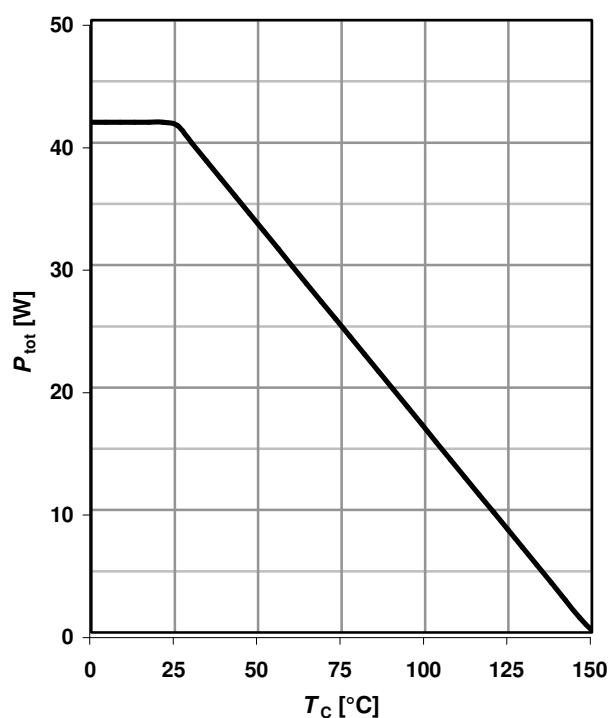
⁵⁾ Device on 40mm*40mm*1.5 epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air

⁶⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

⁷⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

1 Power dissipation

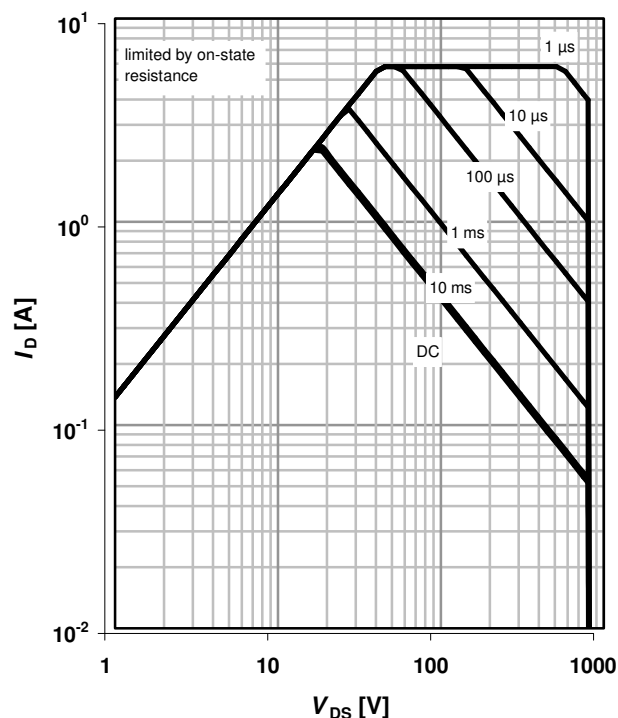
$$P_{\text{tot}} = f(T_C)$$



2 Safe operating area

$$I_D = f(V_{DS}); T_C = 25^\circ\text{C}; D = 0$$

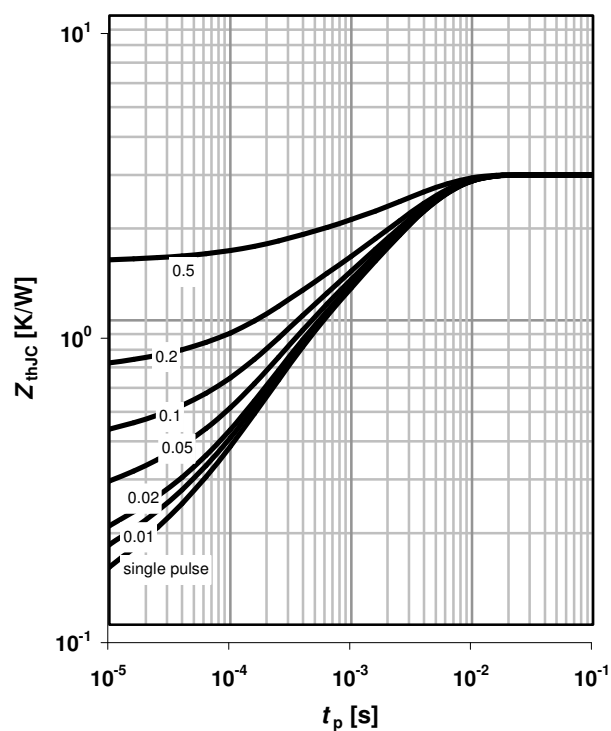
parameter: t_p



3 Max. transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

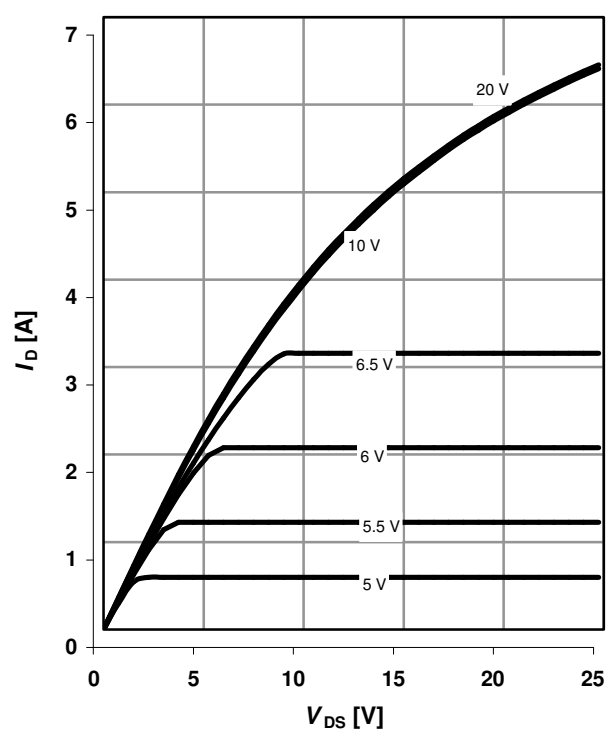
parameter: $D = t_p / T$



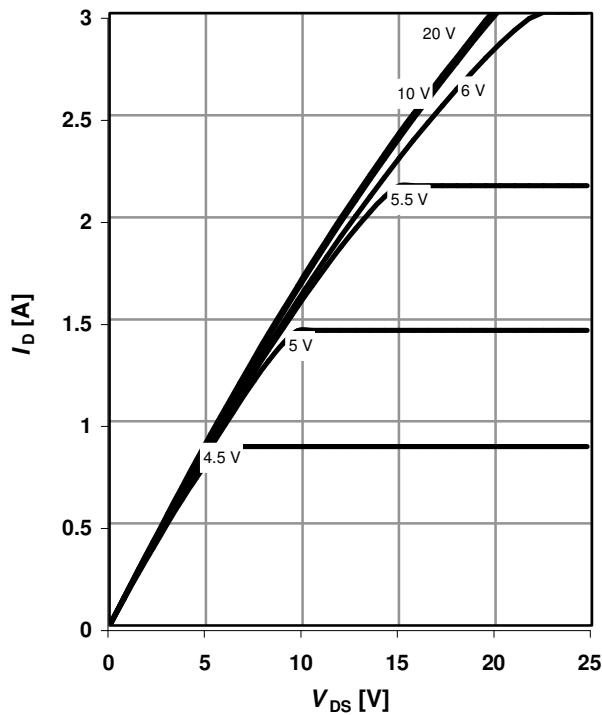
4 Typ. output characteristics

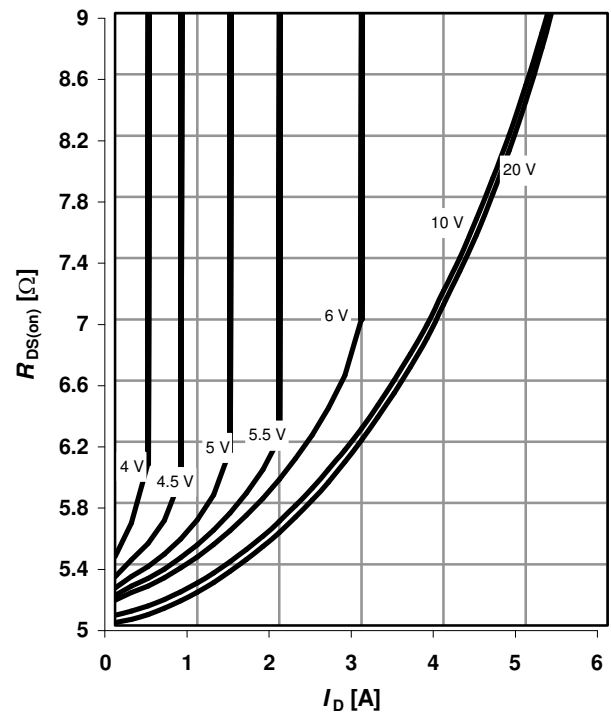
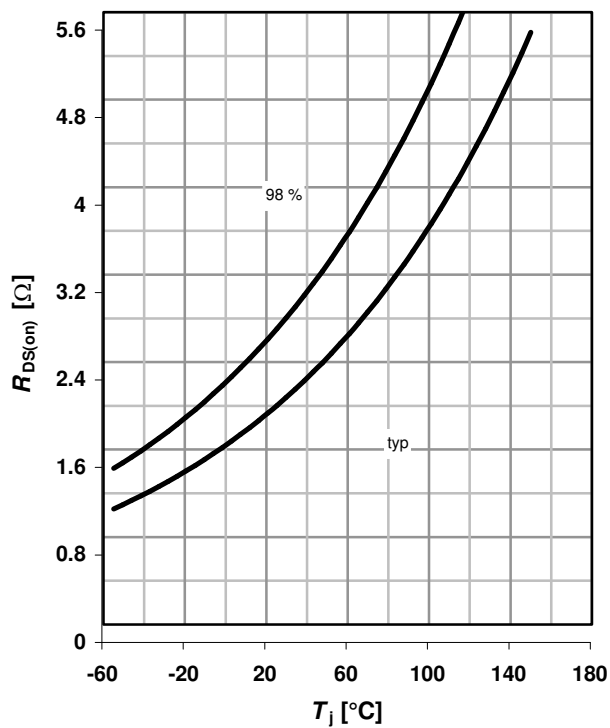
$$I_D = f(V_{DS}); T_J = 25^\circ\text{C}; t_p = 10 \mu\text{s}$$

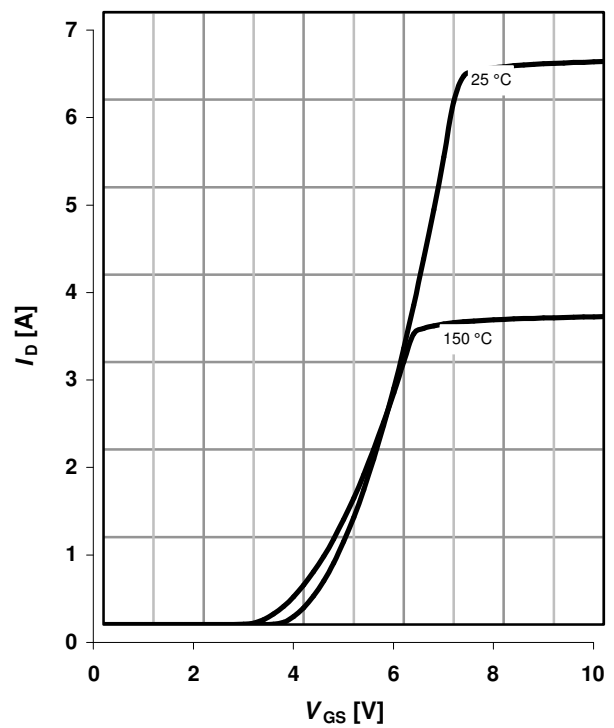
parameter: V_{GS}



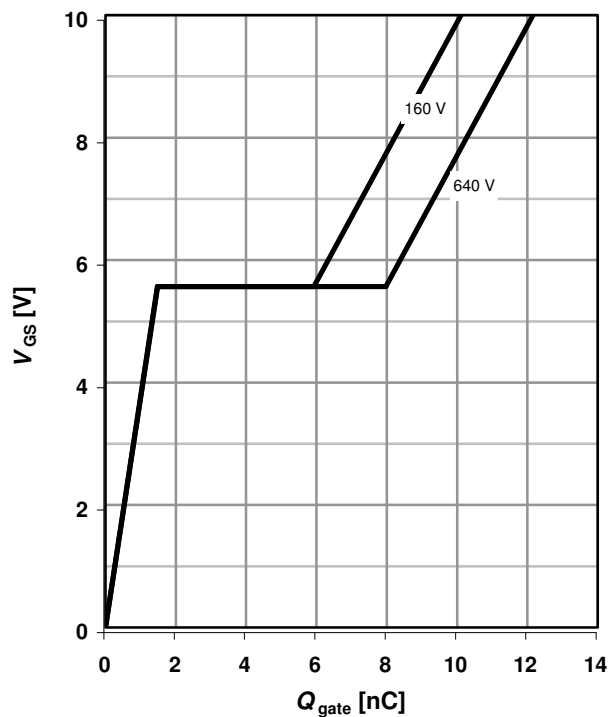
5 Typ. output characteristics
 $I_D = f(V_{DS}); T_j = 150\text{ °C}; t_p = 10\text{ }\mu\text{s}$

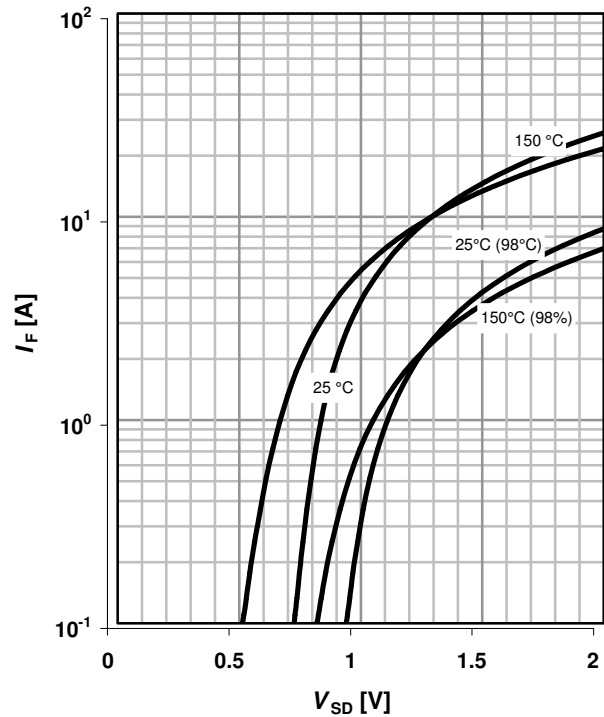
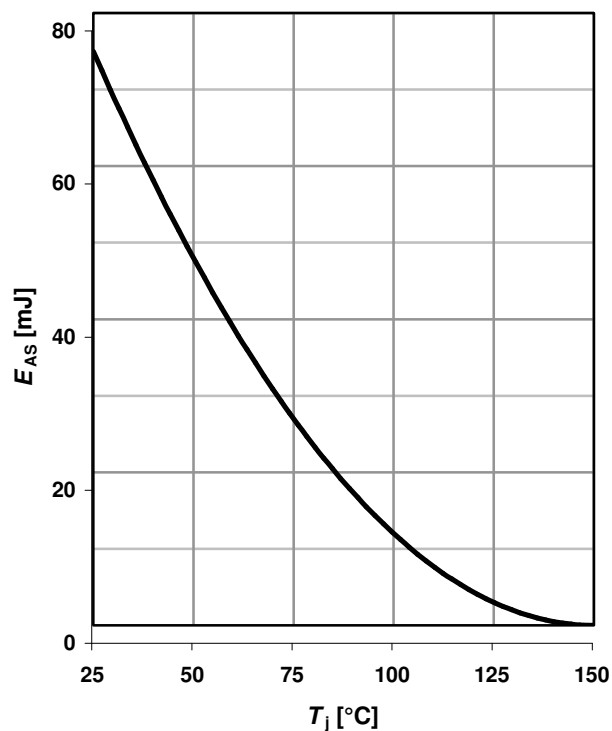
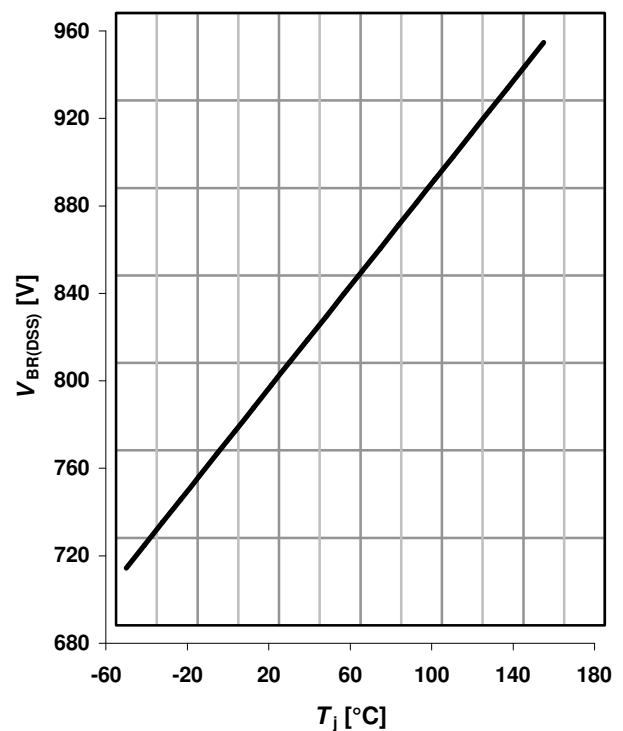
parameter: V_{GS}

6 Typ. drain-source on-state resistance
 $R_{DS(on)} = f(I_D); T_j = 150\text{ °C}$

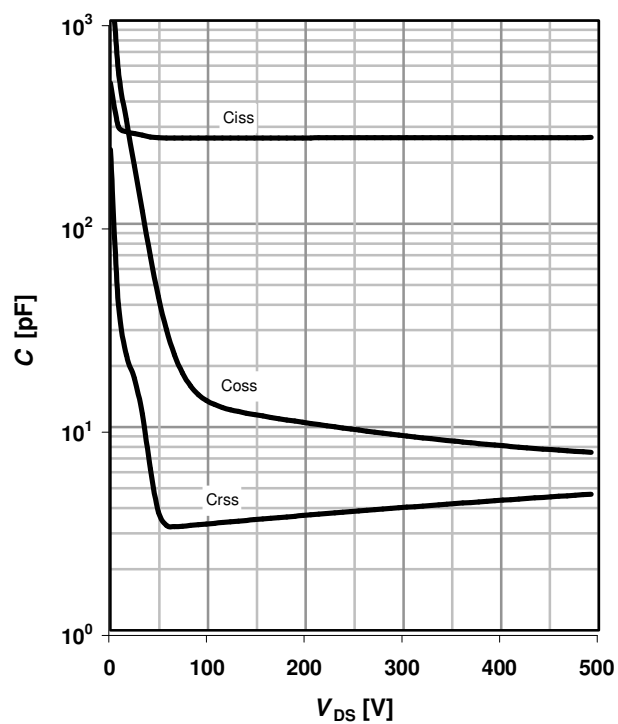
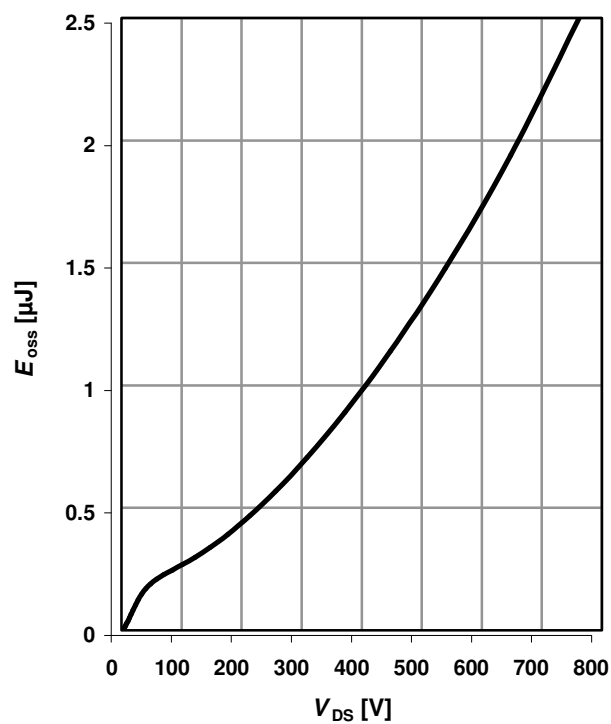
parameter: V_{GS}

7 Drain-source on-state resistance
 $R_{DS(on)} = f(T_j); I_D = 1.2\text{ A}; V_{GS} = 10\text{ V}$

8 Typ. transfer characteristics
 $I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}; t_p = 10\text{ }\mu\text{s}$

parameter: T_j


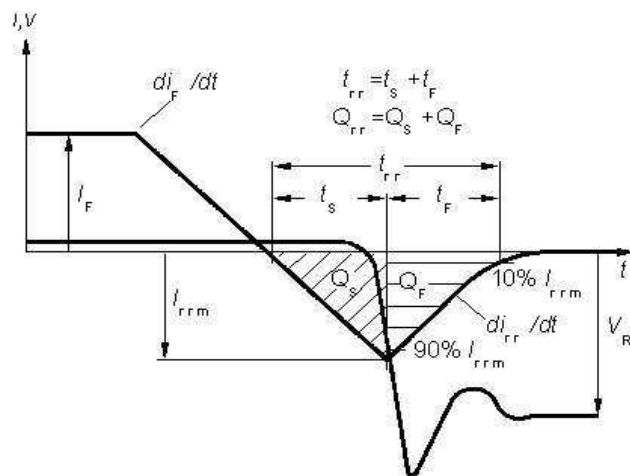
9 Typ. gate charge
 $V_{GS}=f(Q_{gate}); I_D=2\text{ A pulsed}$

parameter: V_{DD}

10 Forward characteristics of reverse diode
 $I_F=f(V_{SD}); t_p=10\text{ }\mu\text{s}$

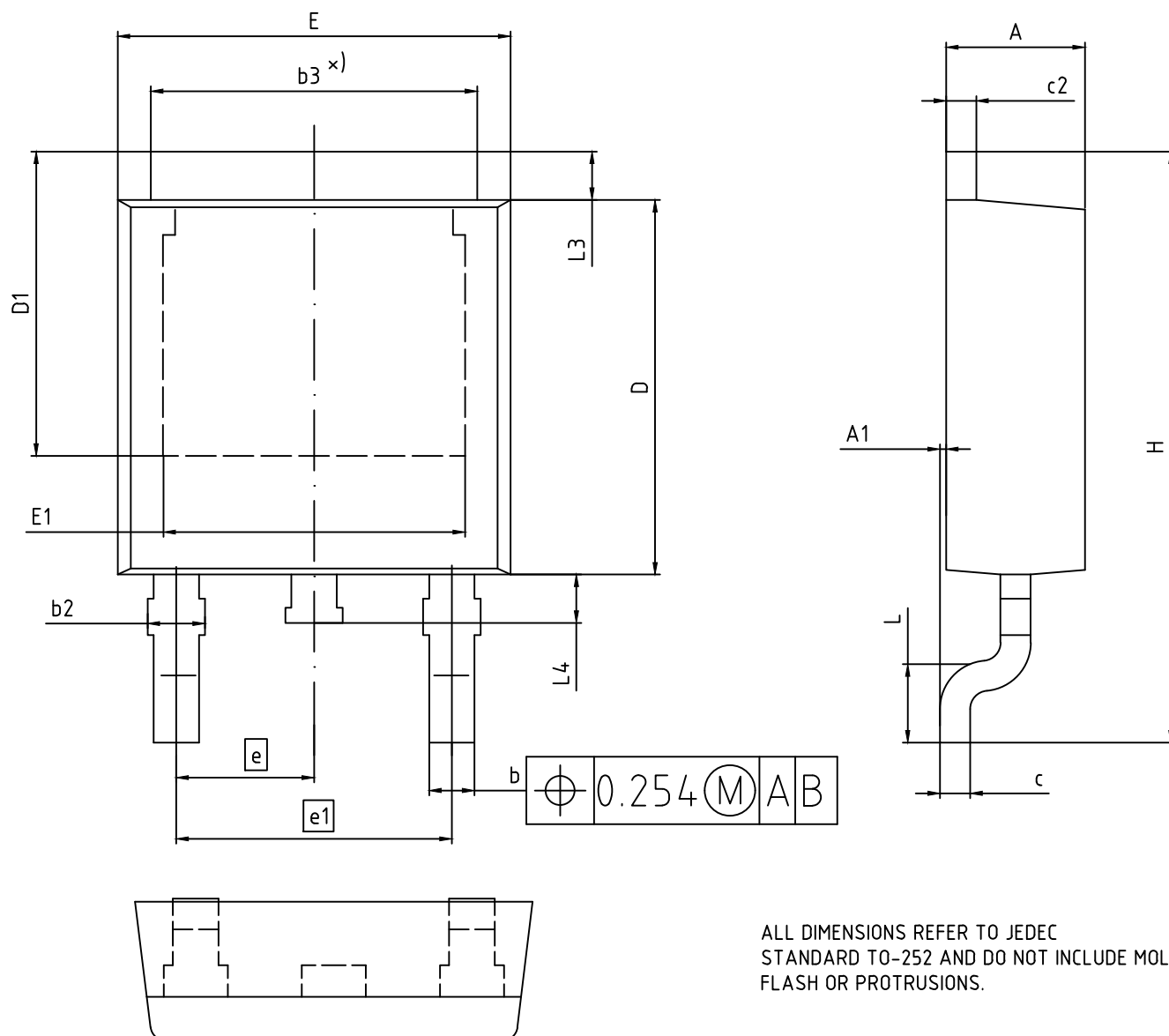
parameter: T_j

11 Avalanche energy
 $E_{AS}=f(T_j); I_D=1\text{ A}; V_{DD}=50\text{ V}$

12 Drain-source breakdown voltage
 $V_{BR(DSS)}=f(T_j); I_D=0.25\text{ mA}$


13 Typ. capacitances
 $C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$

14 Typ. Coss stored energy
 $E_{oss}=f(V_{DS})$


Definition of diode switching characteristics

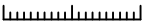
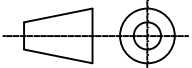


PG-TO252-3-1: Outline , PG-TO-252-3-11 (D-PAK), PG-TO-252-3-21 (D-PAK)



ALL DIMENSIONS REFER TO JEDEC
STANDARD TO-252 AND DO NOT INCLUDE MOLD
FLASH OR PROTRUSIONS.

DIMENSION	MILLIMETERS	
	MIN.	MAX.
A	2.16	2.41
A1	0.00	0.15
b	0.64	0.89
b2	0.65	1.15
b3	4.95	5.50
c	0.46	0.61
c2	0.40	0.98
D	5.97	6.22
D1	5.02	5.84
E	6.35	6.73
E1	4.32	5.50
e	2.29	
e1	4.57	
N	3	
H	9.40	10.48
L	1.18	1.78
L3	0.89	1.27
L4	0.51	1.02

DOCUMENT NO. Z8B00003328
REVISION 07
SCALE: 10:1 0 1 2mm 
EUROPEAN PROJECTION 
ISSUE DATE 01.04.2020

Revision History

SPD02N80C3

Revision: 2020-05-26, Rev. 2.94

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.93	2016-04-19	Non-halogen free version discontinued (creation:2016-04-13)
2.94	2020-05-26	Update package outline

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Published by

Infineon Technologies AG

81726 München, Germany

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